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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	S08
Core Size	8-Bit
Speed	40MHz
Connectivity	I²C, LINbus, SCI, SPI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	30
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Through Hole
Package / Case	32-SDIP (0.400", 10.16mm)
Supplier Device Package	32-SDIP
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08sv8cbm

Table of Contents

Revision History

To provide the most up-to-date information, the revision of our documents on the World Wide Web will be the most current. Your printed copy may be an earlier revision. To verify you have the latest information available, refer to:

http://freescale.com/

The following revision history table summarizes changes contained in this document.

Rev	Date	Description of Changes
1	4/2/2009	Initial public release.
2	7/20/2009	Updated Section 5.13, “EMC Performance.” Corrected Table 1. Corrected default trim value to 31.25 kHz.

Related Documentation

Find the most current versions of all documents at: http://www.freescale.com

Reference Manual (MC9S08SV16RM)

Contains extensive product information including modes of operation, memory, resets and interrupts, register definition, port pins, CPU, and all module information.

1 MCU Block Diagram

The block diagram, Figure 1, shows the structure of MC9S08SV16 series MCU.

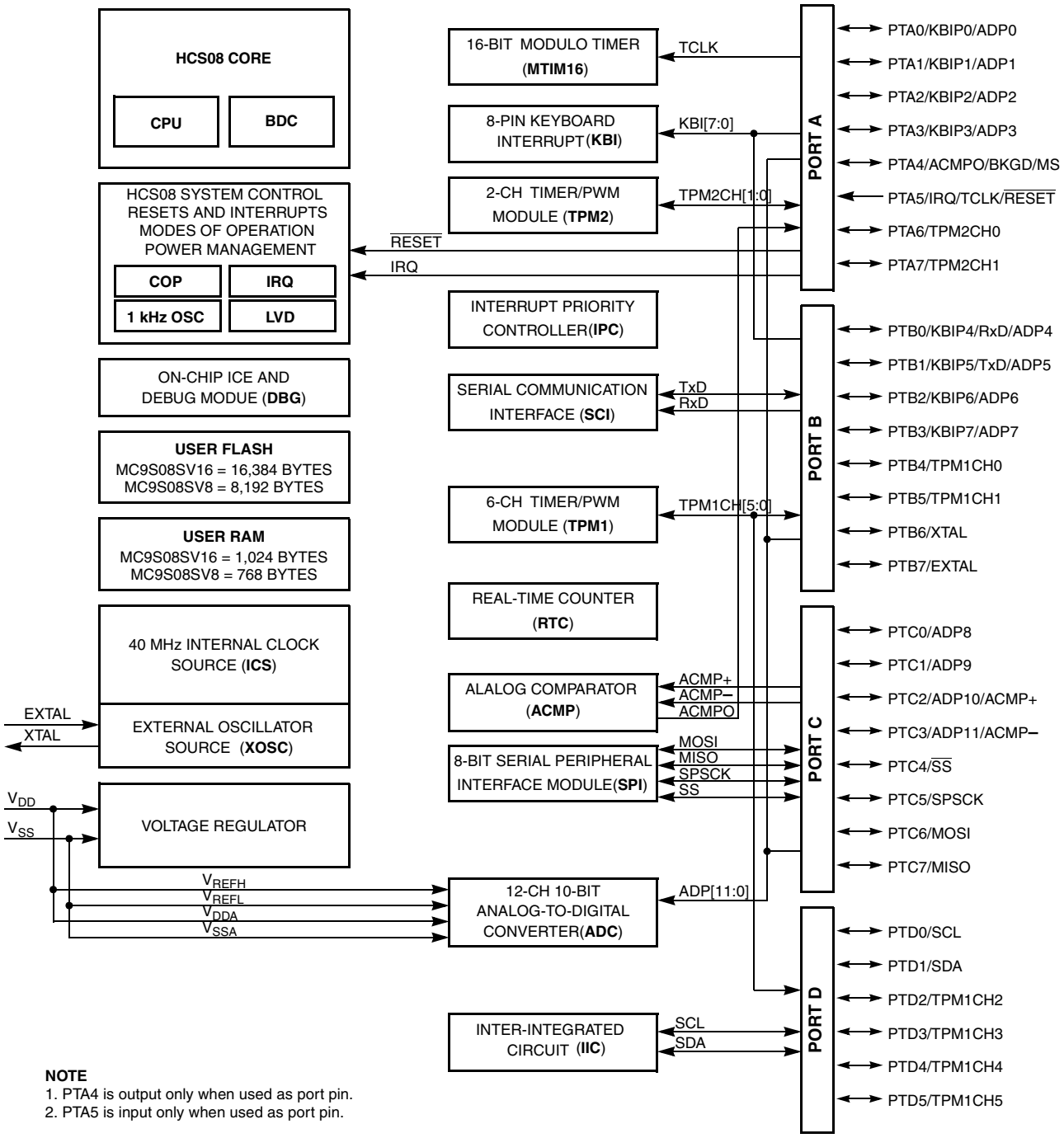


Figure 1. MC9S08SV16 Series Block Diagram

2 System Clock Distribution

MC9S08SV16 series use ICS module as clock sources. The ICS module can use internal or external clock source as reference to provide up to 40 MHz CPU clock. The output of ICS module includes,

- OSCOUT— XOSC output provides EXTAL reference clock to ADC and RTC.
- ICSIRCLK — ICS internal clock reference provides clock source of RTC.
- ICSFFCLK — ICS fixed frequency clock reference (around 32.768 kHz) provides double of the fixed lock signal to TPMs and MTIM16.
- ICSOUT — ICS CPU clock provides double of bus clock which is basic clock reference of peripherals.
- ICSLCLK — Alternate BDC clock provides debug signal to BDC module.

The TCLK pin is an extra external clock source. When TCLK is enabled, it can provide alternate clock source to TPMs and MTIM16. The on-chip 1 kHz clock can provide clock source of RTC and COP modules.

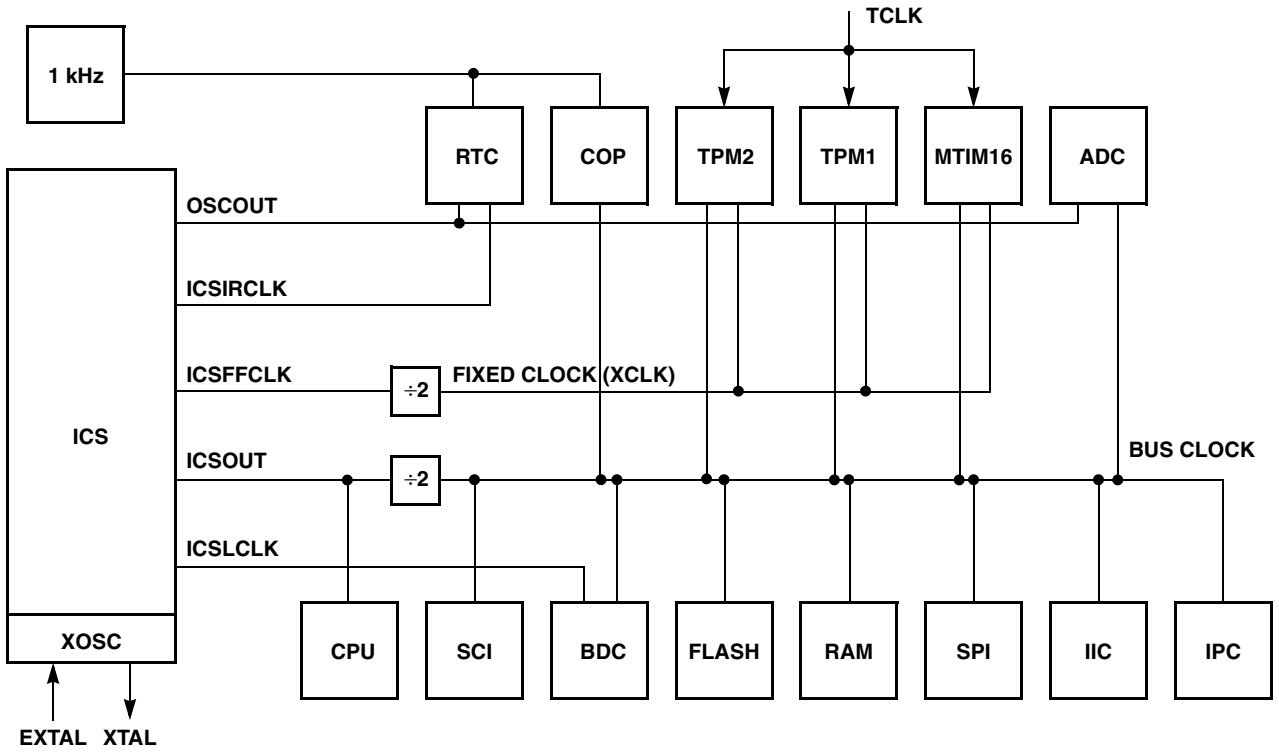


Figure 2. System Clock Distribution Diagram

3 Pin Assignments

This section shows the pin assignments for the MC9S08SV16 series devices.

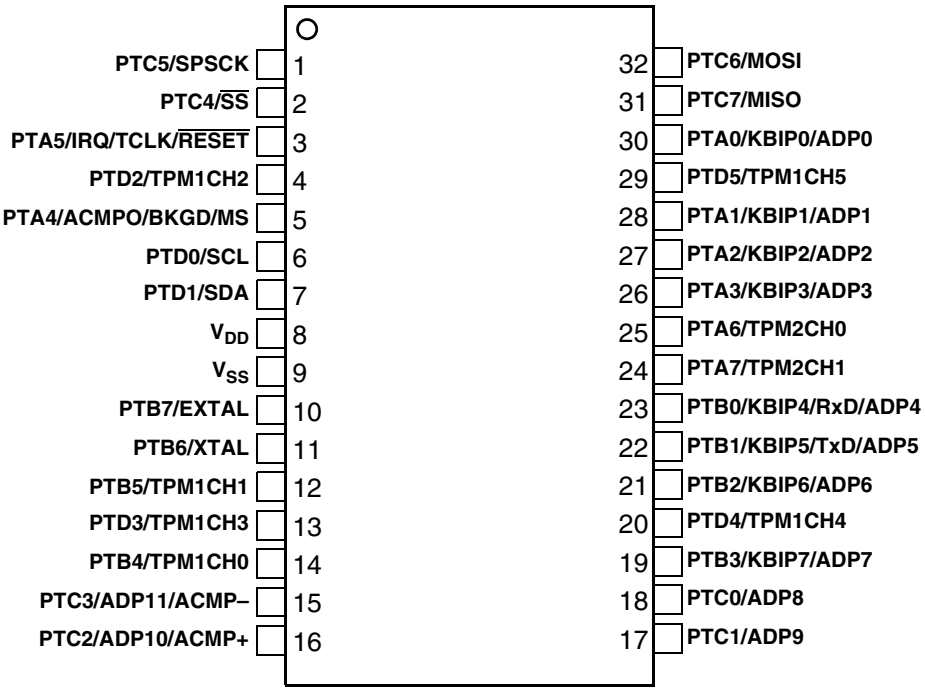


Figure 3. MC9S08SV16 Series 32-Pin SDIP Package

Table 1. Pin Availability by Package Pin-Count (continued)

Pin Number		<-- Lowest **Priority** --> Highest							
32-SDIP	**32-LQFP**	**Port Pin**	**I/O**	**Alt 1**	**I/O**	**Alt 2**	**I/O**	**Alt 3**	**I/O**
15	11	PTC3	I/O			ADP11	I	ACMP–	I
16	12	PTC2	I/O			ADP10	I	ACMP+	I
17	13	PTC1	I/O			ADP9	I		
18	14	PTC0	I/O			ADP8	I		
19	15	PTB3	I/O	KBIP7	I	ADP7	I		
20	16	PTD4	I/O			TPM1CH4	I/O		
21	17	PTB2	I/O	KBIP6	I	ADP6	I		
22	18	PTB1	I/O	KBIP5	I	TxD	I/O	ADP5	I
23	19	PTB0	I/O	KBIP4	I	RxD	I	ADP4	I
24	20	PTA7	I/O			TPM2CH1	I/O		
25	21	PTA6	I/O			TPM2CH0	I/O		
26	22	PTA3	I/O	KBIP3	I	ADP3	I		
27	23	PTA2	I/O	KBIP2	I	ADP2	I		
28	24	PTA1	I/O	KBIP1	I	ADP1	I		
29	25	PTD5	I/O			TPM1CH5	I/O		
30	26	PTA0	I/O	KBIP0	I	ADP0	I		
31	27	PTC7	I/O	MISO	I/O				
32	28	PTC6	I/O	MOSI	I/O				

NOTE

When an alternative function is first enabled, it is possible to get a spurious edge to the module. User software must clear out any associated flags before interrupts are enabled. Table 1 illustrates the priority if multiple modules are enabled. The highest priority module will have control over the pin. Selecting a higher priority pin function with a lower priority function already enabled can cause spurious edges to the lower priority module. Disable all modules that share a pin before enabling another module.

4 Memory Map

Figure 5 shows the memory map for the MC9S08SV16 series. On-chip memory in the MC9S08SV16 series of MCUs consist of RAM, flash program memory for nonvolatile data storage, plus I/O and control/status registers. The registers are divided into two groups:

- Direct-page registers (0x0000 through 0x003F)
- High-page registers (0x1800 through 0x187F)

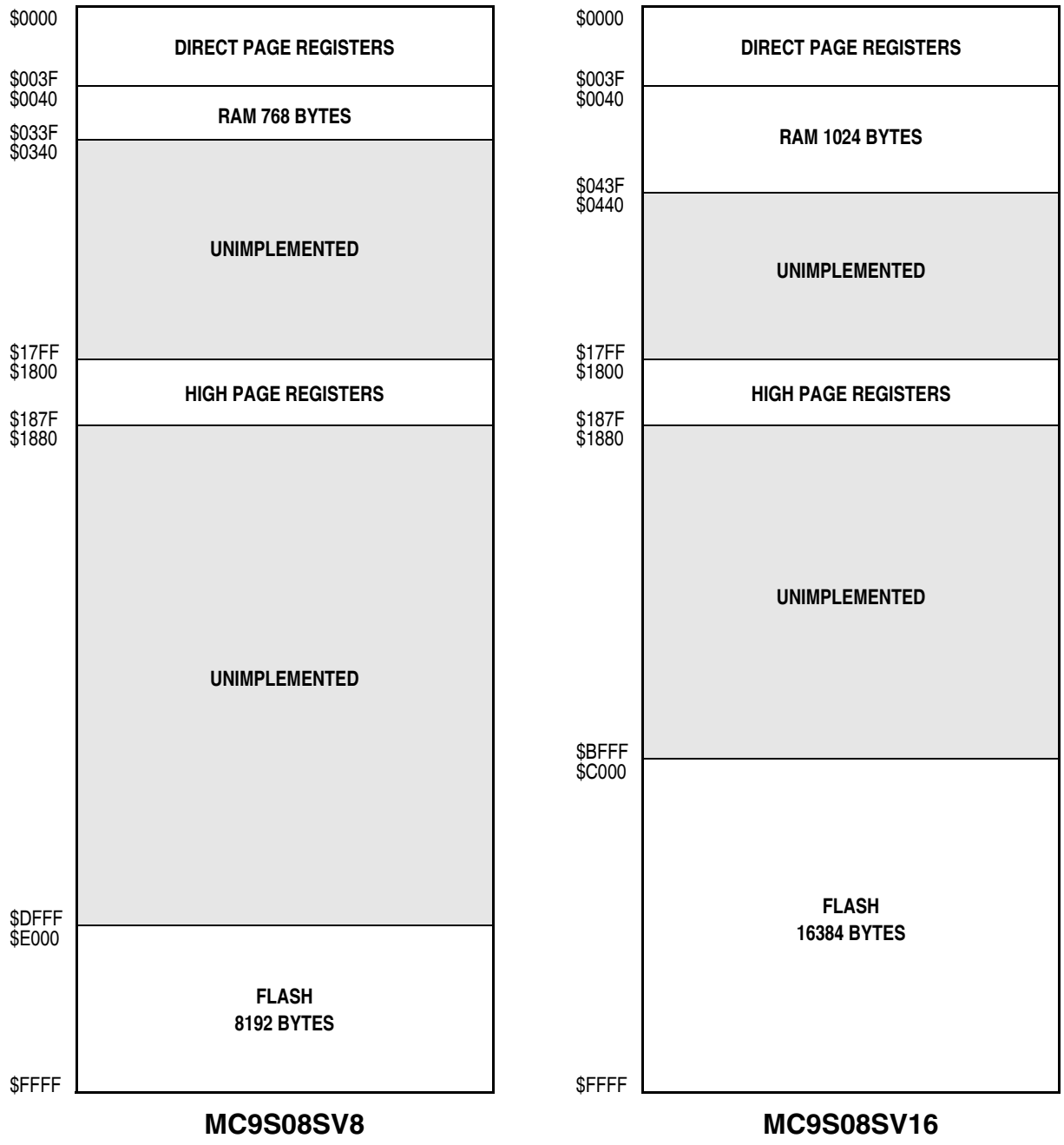


Figure 5. MC9S08SV16 Series Memory Map

5 Electrical Characteristics

5.1 Introduction

This section contains electrical and timing specifications for the MC9S08SV16 series of microcontrollers available at the time of publication.

5.2 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 2. Parameter Classifications

P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

5.3 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 3 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pullup resistor associated with the pin is enabled.

Table 3. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to 5.8	V
Maximum current into V_{DD}	I_{DD}	120	mA
Digital input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	±25	mA
Storage temperature range	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins, except for PTA5 are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current (V_{In} > V_{DD}) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

5.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 4. Thermal Characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T_A	T_L to T_H –40 to 85	°C
Thermal resistance Single-layer board			
32-pin SDIP	θ_{JA}	60	°C/W
32-pin LQFP		85	
Thermal resistance Four-layer board			
32-pin LQFP	θ_{JA}	35	°C/W
32-pin LQFP		56	

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \qquad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C
θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W
$P_D = P_{int} + P_{I/O}$
$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power
$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from Equation 3 by measuring P_D (at equilibrium) for an known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

5.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions must be taken to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

During the device qualification, ESD stresses were performed for the human body model (HBM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless instructed otherwise in the device specification.

Table 5. ESD and Latch-Up Test Conditions

Model	Description	Symbol	Value	Unit
Human body	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	1	—
Latch-up	Minimum input voltage limit	—	–2.5	V
	Maximum input voltage limit	—	7.5	V

Table 7. DC Characteristics (continued)

Num	C	Characteristic	Symbol	Condition	Min.	Typical[1]	Max.	Unit
11a	P	Pullup, pulldown resistors — All digital inputs, when enabled (all I/O pins other than PTA5/IRQ/TCLK/$\overline{\text{RESET}}$)	R_{PU}, R_{PD}	—	17.5	—	52.5	kΩ
11b	C	Pullup, pulldown resistors — (PTA5/IRQ/TCLK/$\overline{\text{RESET}}$)	R_{PU}, R_{PD} (Note[2])	—	17.5	—	52.5	kΩ
12	C	DC injection current [3, 4, 5] — Single pin limit	I_{IC}	$V_{IN} < V_{SS}$, $V_{IN} > V_{DD}$	–0.2	—	0.2	mA
		Total MCU limit, includes sum of all stressed pins			–5	—	5	mA
13	C	Input capacitance, all pins	C_{In}	—	—	—	8	pF
14	C	RAM retention voltage	V_{RAM}	—	—	0.6	1.0	V
15	C	POR re-arm voltage[6]	V_{POR}	—	0.9	1.4	2.0	V
16	D	POR re-arm time	t_{POR}	—	10	—	—	µs
17	P	Low-voltage detection threshold — high range V_{DD} falling V_{DD} rising	V_{LVD1}	—	 3.9 4.0	 4.0 4.1	 4.1 4.2	V
	P	Low-voltage detection threshold — low range V_{DD} falling V_{DD} rising	V_{LVD0}	—	 2.48 2.54	 2.56 2.62	 2.64 2.70	V
18	C	Low-voltage warning threshold — high range 1 V_{DD} falling V_{DD} rising	V_{LVW3}	—	 4.5 4.6	 4.6 4.7	 4.7 4.8	V
	P	Low-voltage warning threshold — high range 0 V_{DD} falling V_{DD} rising	V_{LVW2}	—	 4.2 4.3	 4.3 4.4	 4.4 4.5	V
19	P	Low-voltage warning threshold low range 1 V_{DD} falling V_{DD} rising	V_{LVW1}	—	 2.84 2.90	 2.92 2.98	 3.00 3.06	V
	C	Low-voltage warning threshold — low range 0 V_{DD} falling V_{DD} rising	V_{LVW0}	—	 2.66 2.72	 2.74 2.80	 2.82 2.88	V
21	C	Low-voltage inhibit reset/recover hysteresis	V_{hys}	—	—	80	—	mV
22	C	Bandgap voltage reference[7]	V_{BG}	—	—	1.21	—	V

1 Typical values are measured at 25 °C. Characterized, not tested.

2 The specified resistor value is the actual value internal to the device. The pullup or pulldown value may appear higher when measured externally on the pin.

3 All functional non-supply pins, except for PTA5 are internally clamped to V_{SS} and V_{DD}.

4 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

5 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If the positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure that external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).

6 Maximum is highest voltage that POR is guaranteed.

7 Factory trimmed at V_{DD} = 5.0 V, Temp = 25 °C

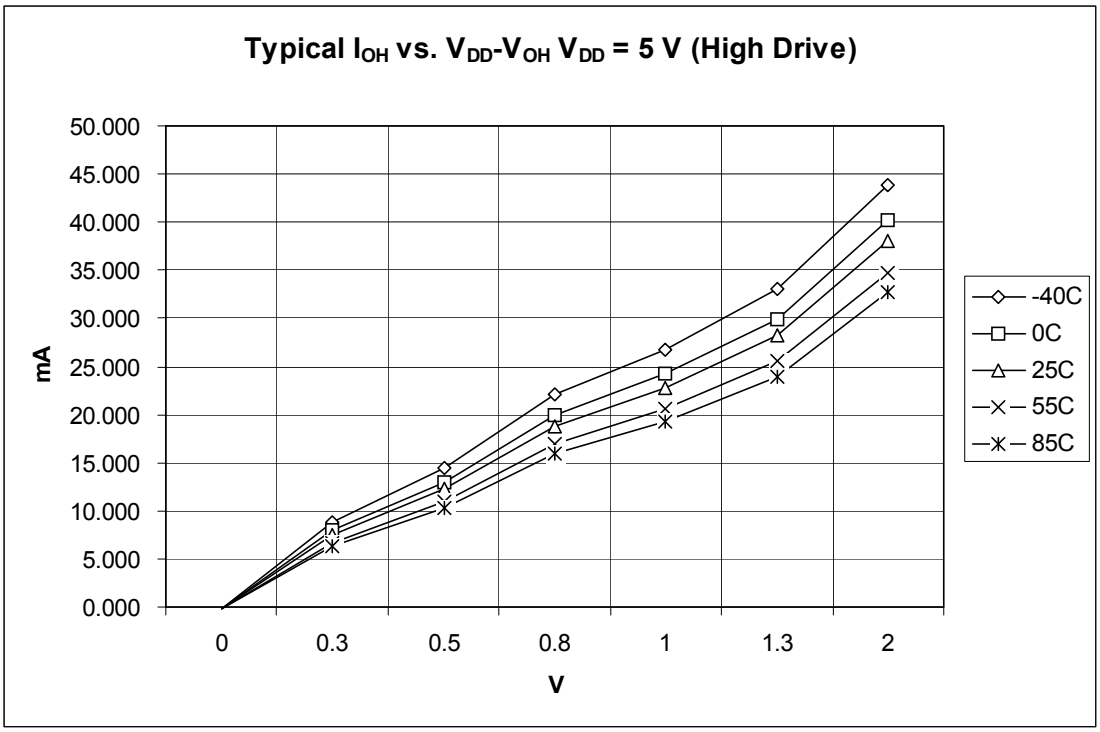


Figure 6. Typical I_{OH} Vs. V_{DD}–V_{OH} (V_{DD} = 5.0 V) (High Drive)

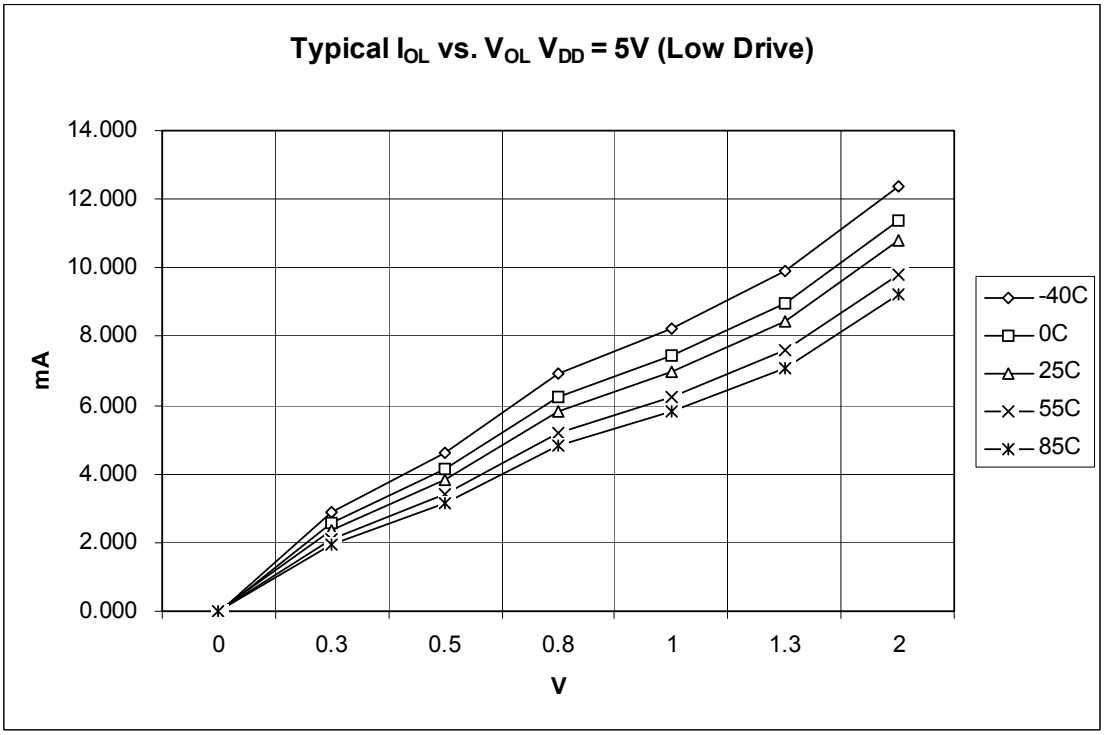


Figure 9. Typical I_{OH} Vs. V_{OL} (V_{DD} = 5.0 V) (Low Drive)

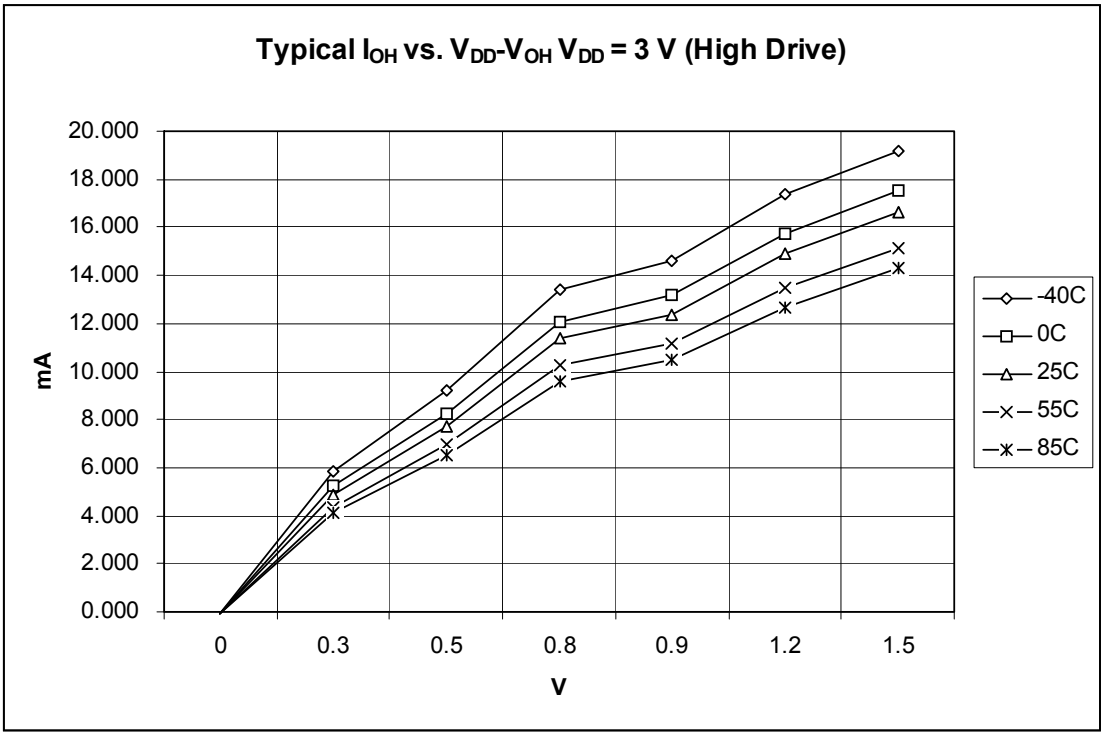


Figure 10. Typical I_{OH} Vs. V_{DD}–V_{OH} (V_{DD} = 3.0 V) (High Drive)

5.9 AC Characteristics

This section describes timing characteristics for each peripheral system.

5.9.1 Control Timing

Table 10. Control Timing

Num	C	Rating	Symbol	Min	Typical[1]	Max	Unit
1	D	Bus frequency ($t_{cyc} = 1/f_{Bus}$)	f_{Bus}	dc	—	20	MHz
2	D	Internal low power oscillator period	t_{LPO}	700	—	1300	µs
3	D	External reset pulse width[2]	t_{extrst}	100	—	—	ns
4	D	Reset low drive	t_{rstdrv}	$34 \times t_{cyc}$	—	—	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t_{MSSU}	500	—	—	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes [3]	t_{MSH}	100	—	—	µs
7	D	IRQ pulse width Asynchronous path[2] Synchronous path[4]	t_{ILIH}, t_{IHIL}	100 $1.5 \times t_{cyc}$	— —	— —	ns
8	D	Keyboard interrupt pulse width Asynchronous path[2] Synchronous path[4]	t_{ILIH}, t_{IHIL}	100 $1.5 \times t_{cyc}$	— —	— —	ns
9	C	Port rise and fall time — Low output drive (PTxDS = 0) (load = 50 pF)[5] Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t_{Rise}, t_{Fall}	— —	16 23	— —	ns
		Port rise and fall time — High output drive (PTxDS = 1) (load = 50 pF)[5] Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t_{Rise}, t_{Fall}	— —	5 9	— —	ns

1 Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

2 This is the shortest pulse that is guaranteed to be recognized as a reset pin request.

3 To enter BDM mode following a POR, BKGD/MS should be held low during the power-up and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.

4 This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized.

5 Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range –40 °C to 85 °C.

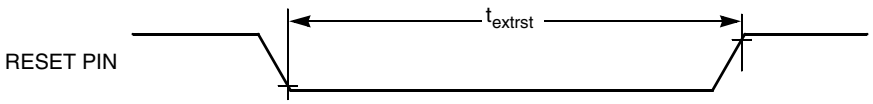


Figure 17. Reset Timing

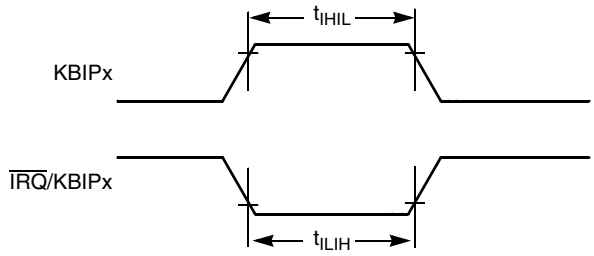


Figure 18. IRQ/KBIPx Timing

5.9.2 TPM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 11. TPM Input Timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

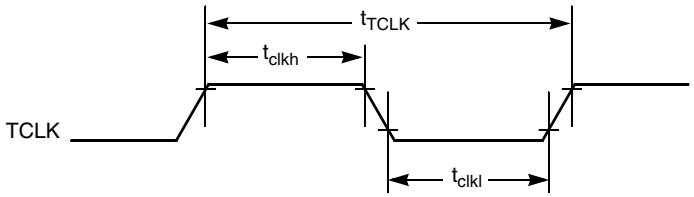


Figure 19. Timer External Clock

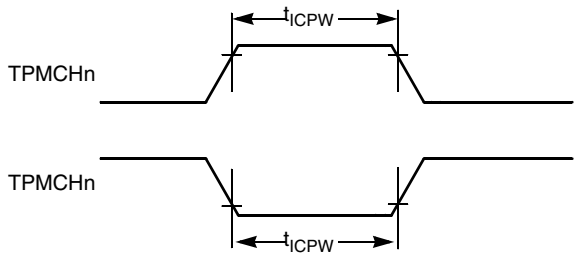
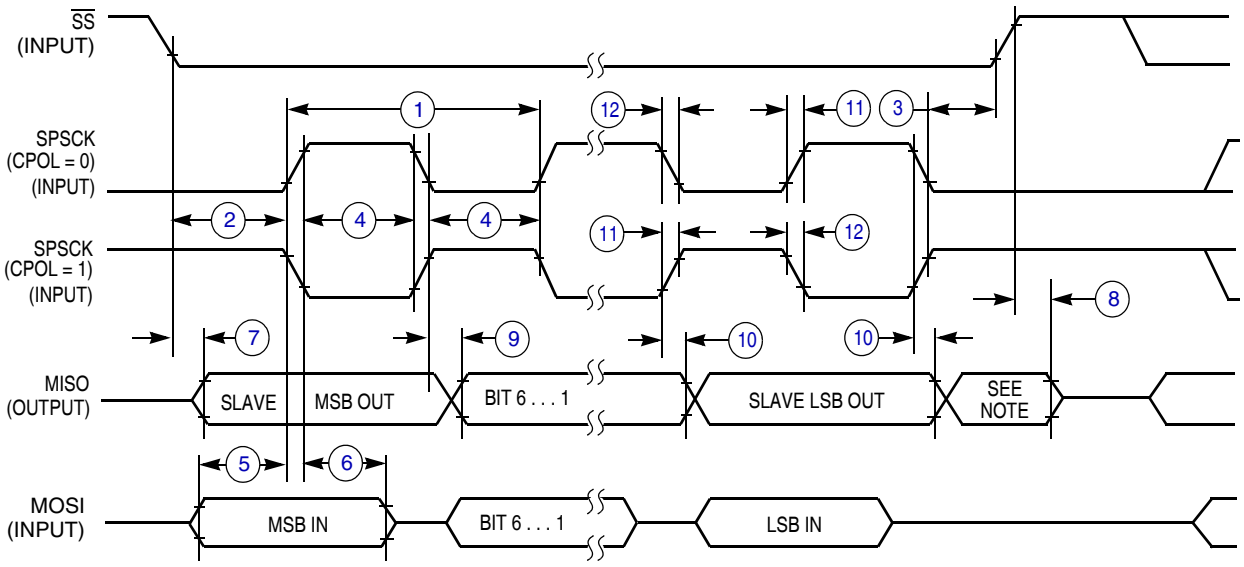


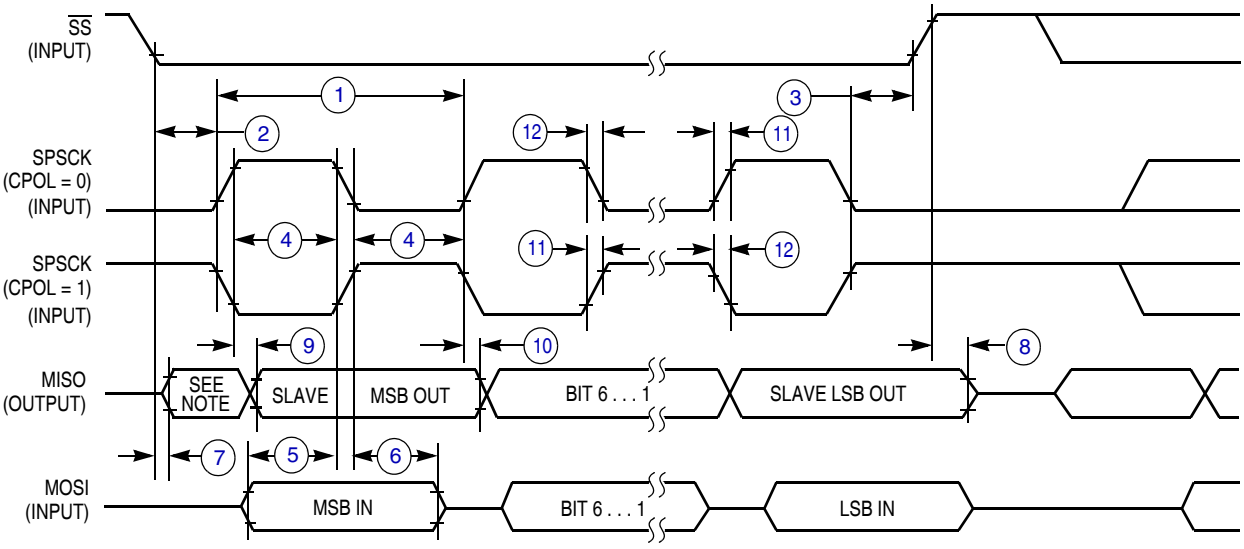
Figure 20. Timer Input Capture Pulse



NOTE:

1. Not defined but normally MSB of character just received

Figure 23. SPI Slave Timing (CPHA = 0)



NOTE:

1. Not defined but normally LSB of character just received

Figure 24. SPI Slave Timing (CPHA = 1)

5.10 Analog Comparator (ACMP) Electricals

Table 13. Analog Comparator Electrical Specifications

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DD}	2.7	—	5.5	V
P	Supply current (active)	I_{DDAC}	—	20	35	µA

Table 13. Analog Comparator Electrical Specifications (continued)

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Analog input voltage	V_{AIN}	V_{SS} – 0.3	—	V_{DD}	V
P	Analog input offset voltage	V_{AIO}	—	20	40	mV
C	Analog comparator hysteresis	V_H	3.0	9.0	15.0	mV
P	Analog input leakage current	I_{ALKG}	—	—	1.0	μA
C	Analog comparator initialization delay	t_{AINIT}	—	—	1.0	μs

5.11 ADC Characteristics

Table 14. 10-Bit ADC Operating Conditions

Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
Supply voltage	Absolute	V_{DDA}	2.7	—	5.5	V	
Input voltage		V_{ADIN}	V_{REFL}	—	V_{REFH}	V	
Input capacitance		C_{ADIN}	—	4.5	5.5	pF	
Input resistance		R_{ADIN}	—	3	5	kΩ	
Analog source resistance	10-bit mode f_{ADCK} > 4MHz f_{ADCK} < 4MHz	R_{AS}	— —	— —	5 10	kΩ	External to MCU
	8-bit mode (all valid f_{ADCK})		—	—	10		
ADC conversion clock frequency	High speed (ADLPC = 0)	f_{ADCK}	0.4	—	8.0	MHz	
	Low power (ADLPC = 1)		0.4	—	4.0		

1 Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

Table 16. Flash Characteristics

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage for program/erase –40 °C to 85 °C	$V_{prog/erase}$	2.7	—	5.5	V
D	Supply voltage for read operation	V_{Read}	2.7	—	5.5	V
D	Internal FCLK frequency[1]	f_{FCLK}	150	—	200	kHz
D	Internal FCLK period (1/FCLK)	t_{Fcyc}	5	—	6.67	µs
P	Byte program time (random location)[2]	t_{prog}	9			t_{Fcyc}
P	Byte program time (burst mode)[2]	t_{Burst}	4			t_{Fcyc}
P	Page erase time[2]	t_{Page}	4000			t_{Fcyc}
P	Mass erase time[2]	t_{Mass}	20,000			t_{Fcyc}
C	Byte program current[3]	RI_{DDBP}	—	4	—	mA
C	Page erase current[3]	RI_{DDPE}	—	6	—	mA
C	Program/erase endurance[4] T_L to T_H = –40 °C to 85 °C T = 25 °C		10,000	— 100,000	— —	cycles
C	Data retention[5]	t_{D_ret}	15	100	—	years

1 The frequency of this clock is controlled by a software setting.

2 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

3 The program and erase currents are additional to the standard run I_{DD}. These values are measured at room temperatures with V_{DD} = 5.0 V, bus frequency = 4.0 MHz.

4 **Typical endurance for flash** was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale defines typical endurance, please refer to Engineering Bulletin EB619, *Typical Endurance for Nonvolatile Memory.*

5 **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25 °C using the Arrhenius equation. For additional information on how Freescale defines typical data retention, please refer to Engineering Bulletin EB618, *Typical Data Retention for Nonvolatile Memory.*

5.13 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

5.13.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (the North and East).

The maximum radiated RF emissions of the tested configuration in all orientations are less than or equal to the reported emissions levels.

Table 17. Radiated Emissions, Electric Field

Parameter	Symbol	Conditions	Frequency	f_{OSC}/f_{BUS}	Level[1] (Max)	Unit
Radiated emissions, electric field	V_{RE_TEM}	V_{DD} = 5.0 V T_A = 25 °C package type 32-pin LQFP	0.15 – 50 MHz	4 MHz crystal 19 MHz bus	9	dBμV
			50 – 150 MHz		5	
			150 – 500 MHz		2	
			500 – 1000 MHz		1	
			IEC Level		N	—
			SAE Level		1	—

1 Data based on qualification test results.

6 Ordering Information

This section contains ordering information for MC9S08SV16 series devices. See below for an example of the device numbering system.

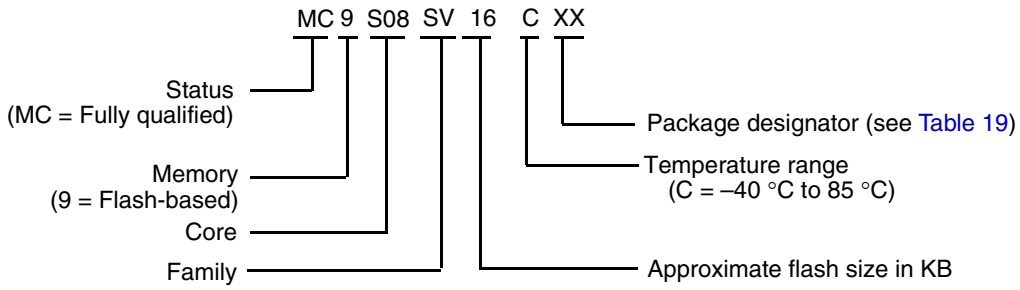
Table 18. Device Numbering System

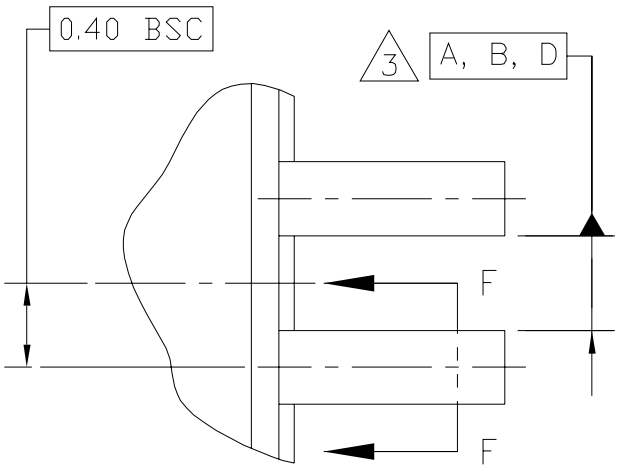
Device Number[1]	Memory		Available Packages[2]
	FLASH	RAM	
MC9S08SV16	16 KB	1024 Byte	32-pin SDIP 32-pin LQFP
MC9S08SV8	8 KB	768 Byte	

1 See the reference manual, *MC9S08SV16 Series Reference Manual*, for a complete description of modules included on each device.

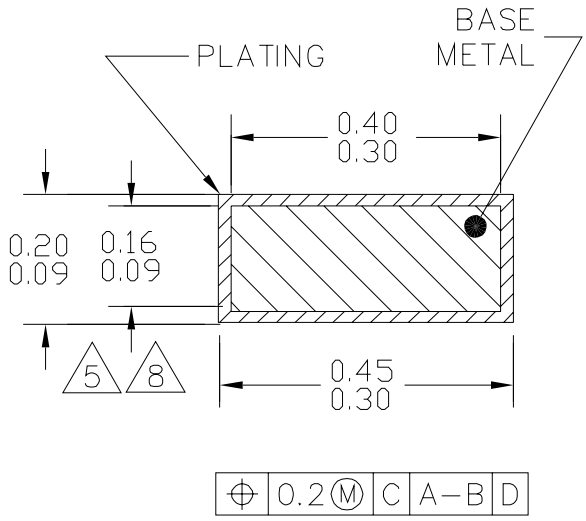
2 See Table 19 for package information.

Example of the device numbering system:

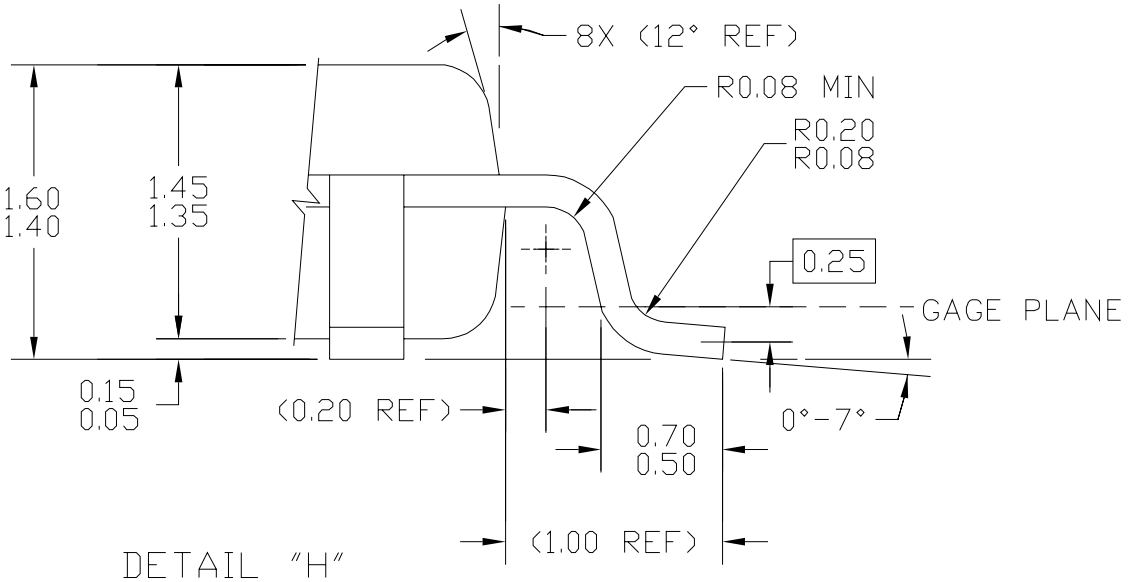




DETAIL G



SECTION F–F
ROTATED 90°CW
32 PLACES



DETAIL "H"

MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

TITLE:	DOCUMENT NO: 98ASH70029A	REV: D
LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5–1994.

3. DATUMS A, B, AND D TO BE DETERMINED AT DATUM PLANE H.

4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE DATUM C.

5. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE MAXIMUM DIMENSION BY MORE THAN 0.08 MM. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION: 0.07 MM.

6. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 MM PER SIDE. DIMENSIONS ARE MAXIMUM PLASTIC BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH.

7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.

8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 MM AND 0.25 MM FROM THE LEAD TIP.

MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

TITLE:	DOCUMENT NO: 98ASH70029A	REV: D
LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	